

62 mm C-Series module with TRENCHSTOP™ IGBT7 and emitter controlled 7 diode

Features

- Electrical features
 - $V_{CES} = 1200\text{ V}$
 - $I_{C\text{nom}} = 450\text{ A} / I_{CRM} = 900\text{ A}$
 - TRENCHSTOP™ IGBT7
 - $V_{CE,\text{sat}}$ with positive temperature coefficient
 - Suitable Infineon gate drivers can be found under <https://www.infineon.com/gdfinder>
- Mechanical features
 - 4 kV AC 1 min insulation
 - High creepage and clearance distances
 - High power density
 - Isolated base plate
 - Package with CTI > 400
 - Standard housing



Typical appearance

Potential applications

- Servo drives
- Solar applications
- UPS systems
- Motor drives
- High-power converters
- Commercial agriculture vehicles
- Three-level applications

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

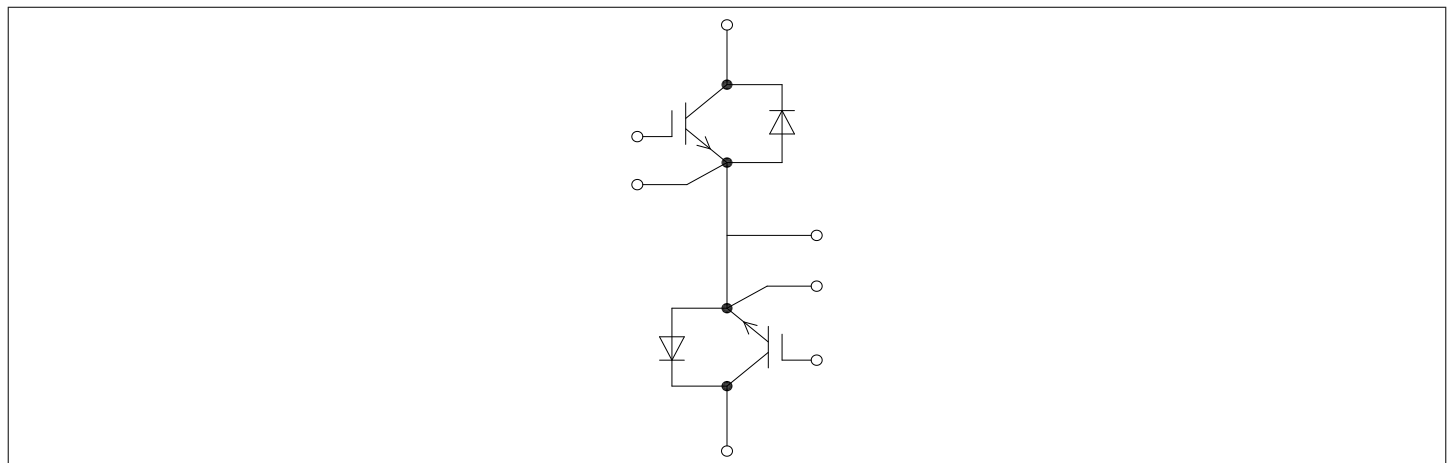


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 60 \text{ s}$	4.0	kV
Material of module baseplate			Cu	
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	29.0	mm
Creepage distance	d_{Creep}	terminal to terminal	23.0	mm
Clearance	d_{Clear}	terminal to heatsink	23.0	mm
Clearance	d_{Clear}	terminal to terminal	11.0	mm
Comparative tracking index	CTI		> 400	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			20		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25 \text{ °C}$, per switch		0.5		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting torque for module mounting	M	- Mounting according to valid application note	M5, Screw	3	6	Nm
Terminal connection torque	M	- Mounting according to valid application note	M6, Screw	2.5	5	Nm
Weight	G			340		g

2 IGBT, T1 / T2

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25 \text{ °C}$	1200	V
Continuous DC collector current	I_{CDC}	$T_{vj \text{ max}} = 175 \text{ °C}$ $T_C = 100 \text{ °C}$	450	A
Maximum RMS module DC-terminal current	I_{tRMS}	$T_{Terminal} = 115 \text{ °C}$, $T_C = 90 \text{ °C}$	650	A
		$T_{Terminal} = 115 \text{ °C}$, $T_C = 115 \text{ °C}$	600	

(table continues...)
 Datasheet

Table 3 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$	900	A
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 450\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$	1.50	1.75	V
			$T_{vj} = 125\ ^\circ C$	1.65		
			$T_{vj} = 150\ ^\circ C$	1.70		
			$T_{vj} = 175\ ^\circ C$	1.75		
Gate threshold voltage	V_{Geth}	$I_C = 9\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.15	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 600\ V$		7.41		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.7		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		70.8		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		0.354		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 1200\ V, V_{GE} = 0\ V$			0.1	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 450\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.370		μs
			$T_{vj} = 125\ ^\circ C$	0.381		
			$T_{vj} = 150\ ^\circ C$	0.385		
			$T_{vj} = 175\ ^\circ C$	0.389		
Rise time (inductive load)	t_r	$I_C = 450\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.51\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.043		μs
			$T_{vj} = 125\ ^\circ C$	0.049		
			$T_{vj} = 150\ ^\circ C$	0.051		
			$T_{vj} = 175\ ^\circ C$	0.052		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 450\ A, V_{CC} = 600\ V, V_{GE} = \pm 15\ V, R_{Goff} = 1.5\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.522		μs
			$T_{vj} = 125\ ^\circ C$	0.588		
			$T_{vj} = 150\ ^\circ C$	0.610		
			$T_{vj} = 175\ ^\circ C$	0.623		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Fall time (inductive load)	t_f	$I_C = 450 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.5 \Omega$	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.124	μs
			$T_{vj} = 125 \text{ }^\circ\text{C}$		0.263	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		0.307	
			$T_{vj} = 175 \text{ }^\circ\text{C}$		0.351	
Turn-on energy loss per pulse	E_{on}	$I_C = 450 \text{ A}, V_{CC} = 600 \text{ V}, L_\sigma = 25 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 0.51 \Omega, di/dt = 6900 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		14.1	mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		22.2	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		25	
			$T_{vj} = 175 \text{ }^\circ\text{C}$		27.7	
Turn-off energy loss per pulse	E_{off}	$I_C = 450 \text{ A}, V_{CC} = 600 \text{ V}, L_\sigma = 25 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.5 \Omega, dv/dt = 3100 \text{ V}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		36.9	mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		58.9	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		65.6	
			$T_{vj} = 175 \text{ }^\circ\text{C}$		72.2	
SC data	I_{SC}	$V_{GE} \leq 15 \text{ V}, V_{CC} = 800 \text{ V}, V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 8 \mu\text{s}, T_{vj} = 150 \text{ }^\circ\text{C}$		1700	A
			$t_p \leq 6 \mu\text{s}, T_{vj} = 175 \text{ }^\circ\text{C}$		1500	
Thermal resistance, junction to case	R_{thJC}	per IGBT			0.0809	K/W
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$			0.0372	K/W
Temperature under switching conditions	$T_{vj op}$		-40		175	$^\circ\text{C}$

Note: $T_{vj op} > 150 \text{ }^\circ\text{C}$ is only allowed for operation at overload conditions. For detailed specifications please refer to AN 2018-14.

3 Diode, D1 / D2

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25 \text{ }^\circ\text{C}$	1200	V
Continuous DC forward current	I_F		450	A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$	900	A

(table continues...)

Table 5 (continued) Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
I^2t - value	I^2t	$t_p = 10 \text{ ms}, V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	14400	A^2s
			$T_{vj} = 175 \text{ }^\circ\text{C}$	10400	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 450 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.80	2.10	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.70		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.65		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		1.60		
Peak reverse recovery current	I_{RM}	$V_{CC} = 600 \text{ V}, I_F = 450 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6900 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		377		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		480		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		509		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		538		
Recovered charge	Q_r	$V_{CC} = 600 \text{ V}, I_F = 450 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6900 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		39.2		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		65.6		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		76.4		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		87.2		
Reverse recovery energy	E_{rec}	$V_{CC} = 600 \text{ V}, I_F = 450 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 6900 \text{ A}/\mu\text{s} (T_{vj} = 175 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$		18		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		32.8		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		37.4		
			$T_{vj} = 175 \text{ }^\circ\text{C}$		41.9		
Thermal resistance, junction to case	R_{thJC}	per diode			0.134	K/W	
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		0.0520		K/W	
Temperature under switching conditions	T_{vjop}		-40		175	$^\circ\text{C}$	

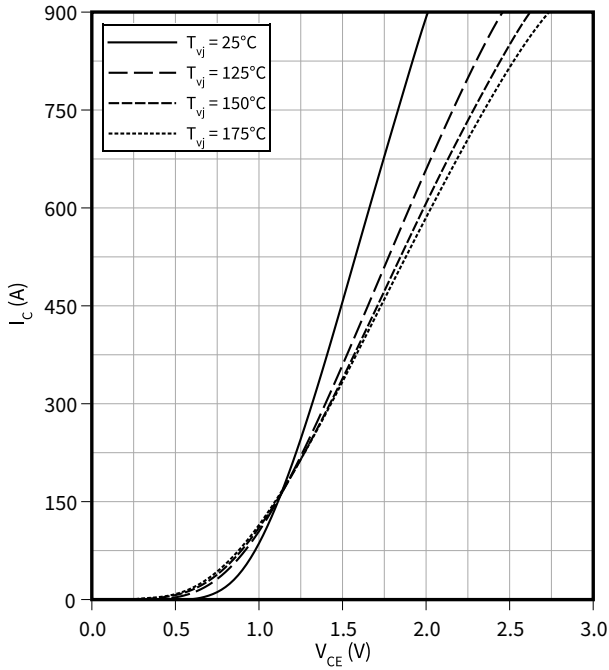
Note: $T_{vjop} > 150 \text{ }^\circ\text{C}$ is only allowed for operation at overload conditions. For detailed specifications please refer to AN 2018-14.

4 Characteristics diagrams

Output characteristic (typical), IGBT, T1 / T2

$$I_C = f(V_{CE})$$

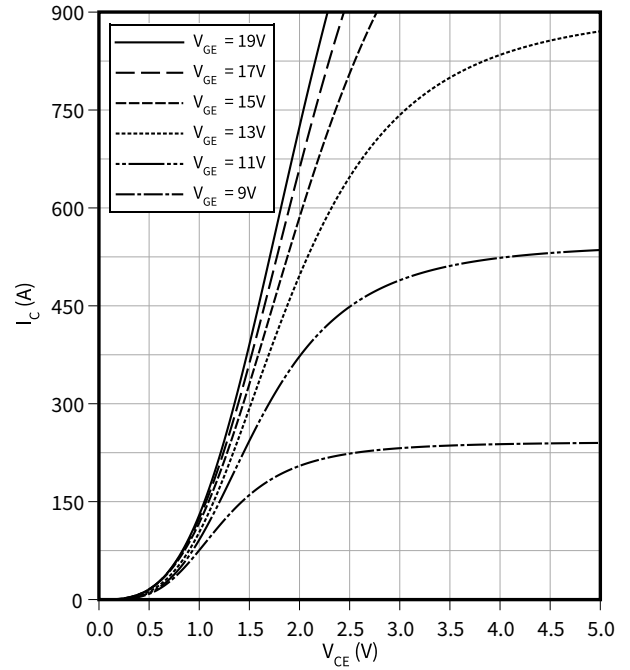
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, T1 / T2

$$I_C = f(V_{CE})$$

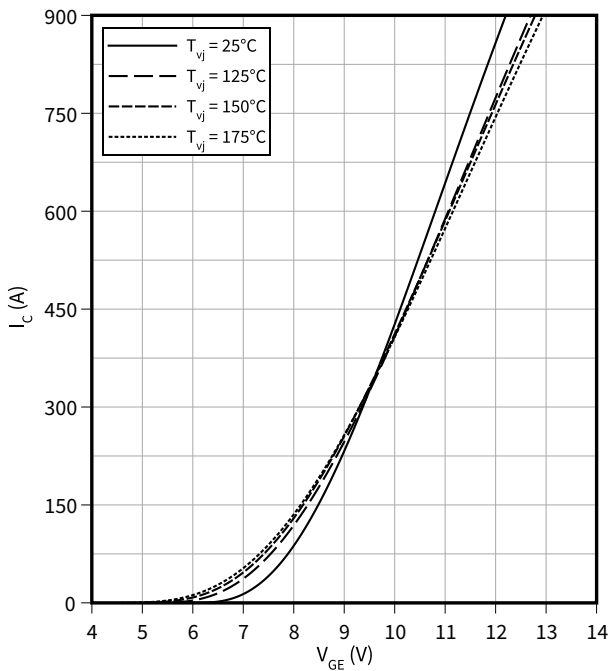
$$T_{vj} = 175 \text{ °C}$$



Transfer characteristic (typical), IGBT, T1 / T2

$$I_C = f(V_{GE})$$

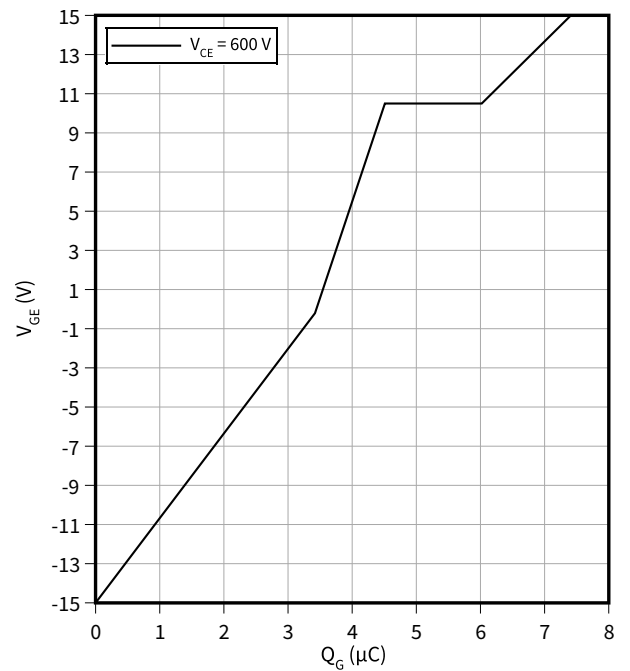
$$V_{CE} = 20 \text{ V}$$



Gate charge characteristic (typical), IGBT, T1 / T2

$$V_{GE} = f(Q_G)$$

$$I_C = 450 \text{ A}, T_{vj} = 25 \text{ °C}$$

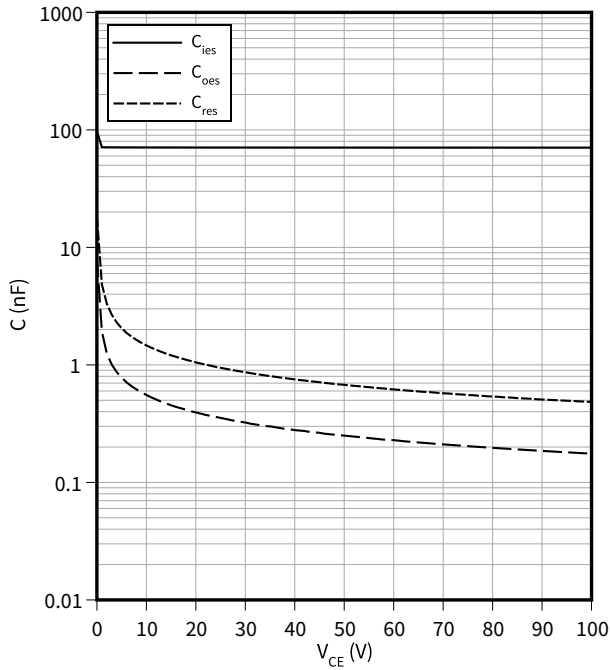


4 Characteristics diagrams

Capacity characteristic (typical), IGBT, T1 / T2

$C = f(V_{CE})$

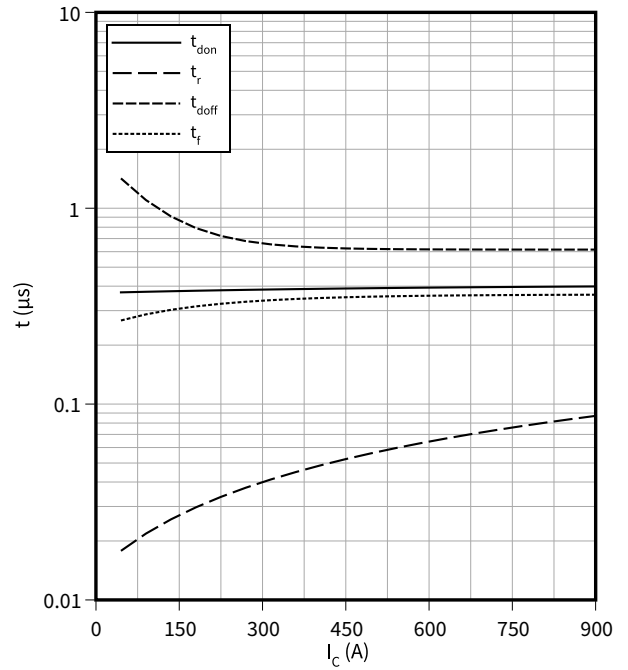
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, T1 / T2

$t = f(I_C)$

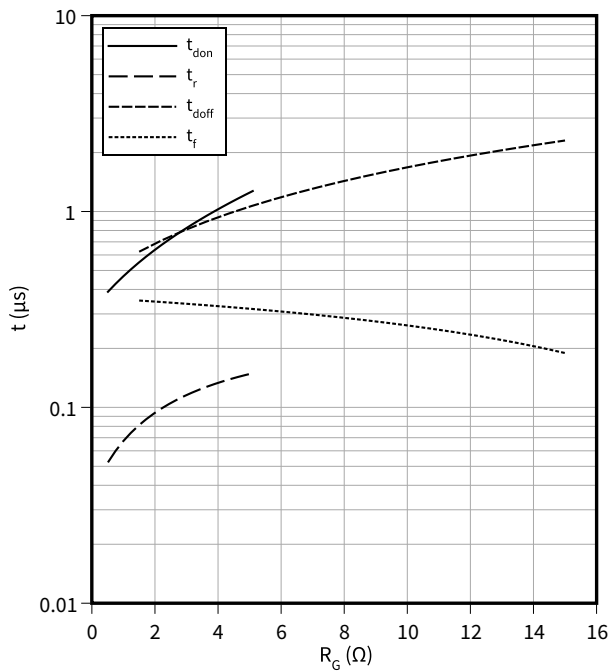
$R_{Goff} = 1.5 \text{ } \Omega, R_{Gon} = 0.51 \text{ } \Omega, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, T1 / T2

$t = f(R_G)$

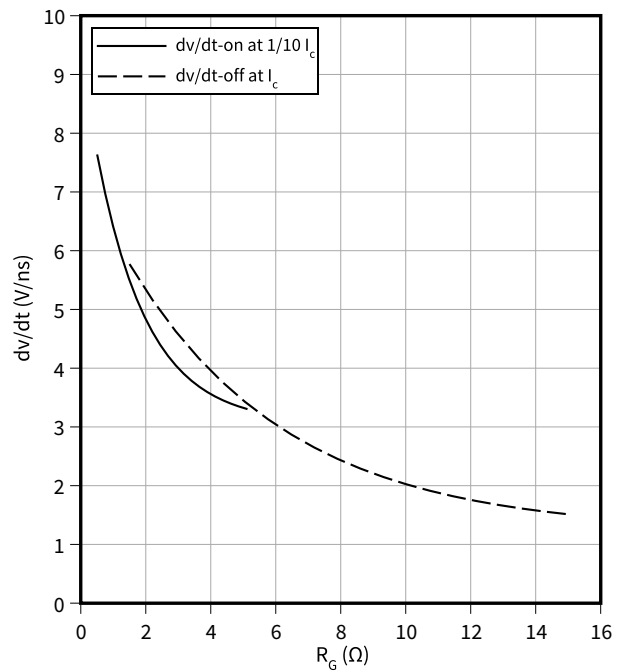
$I_C = 450 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 175 \text{ }^\circ\text{C}$



Voltage slope (typical), IGBT, T1 / T2

$dv/dt = f(R_G)$

$I_C = 450 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$

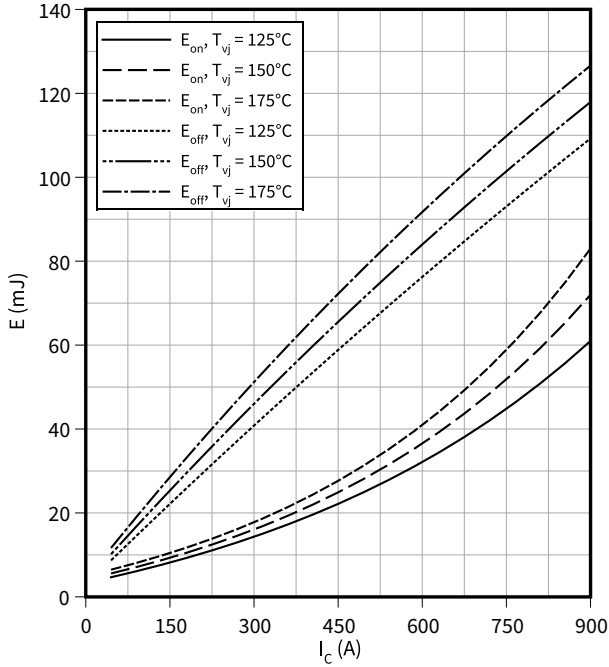


4 Characteristics diagrams

Switching losses (typical), IGBT, T1 / T2

$E = f(I_C)$

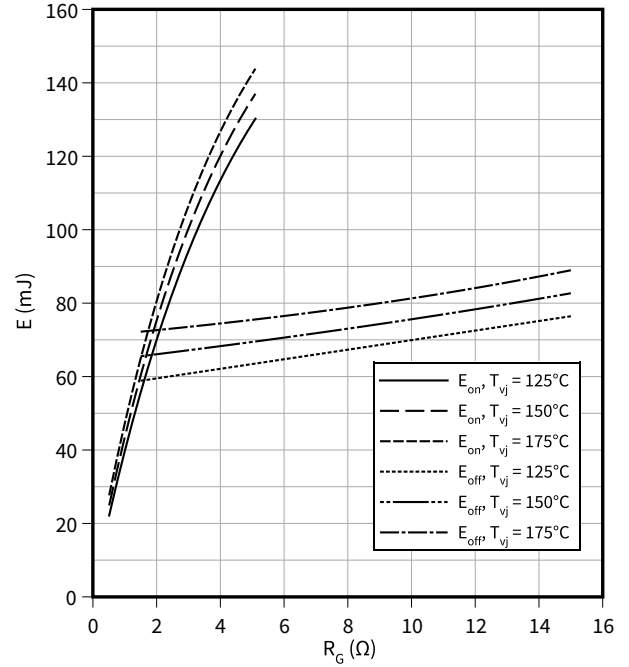
$R_{Goff} = 1.5 \Omega$, $R_{Gon} = 0.51 \Omega$, $V_{CC} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



Switching losses (typical), IGBT, T1 / T2

$E = f(R_G)$

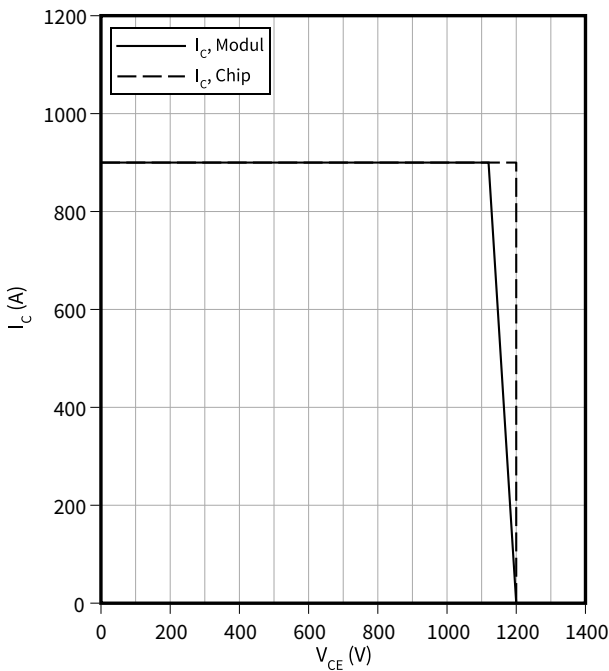
$I_C = 450 \text{ A}$, $V_{CC} = 600 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$



Reverse bias safe operating area (RBSOA), IGBT, T1 / T2

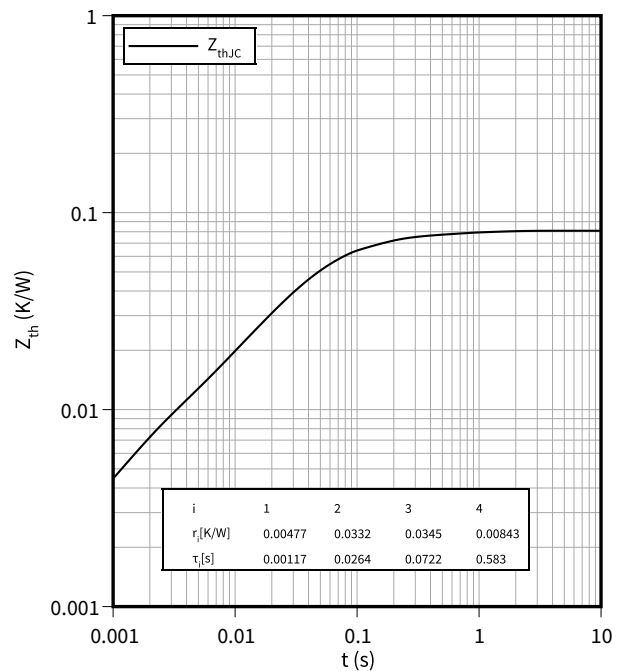
$I_C = f(V_{CE})$

$R_{Goff} = 1.5 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 175 \text{ °C}$



Transient thermal impedance, IGBT, T1 / T2

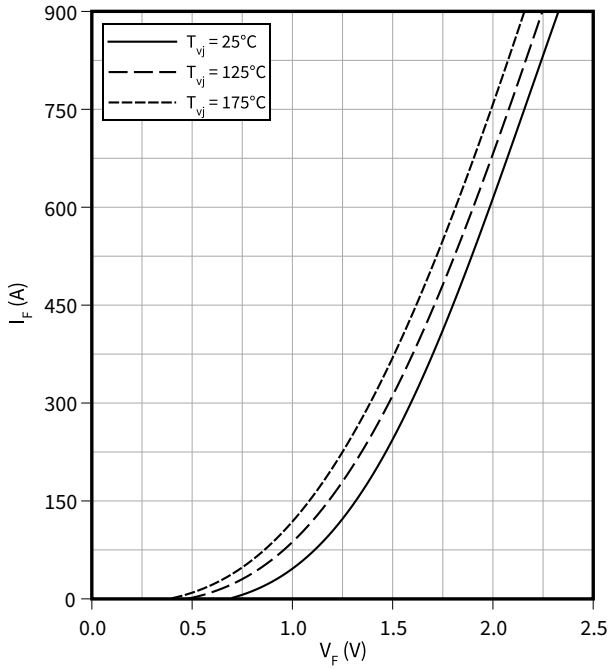
$Z_{th} = f(t)$



4 Characteristics diagrams

Forward characteristic (typical), Diode, D1 / D2

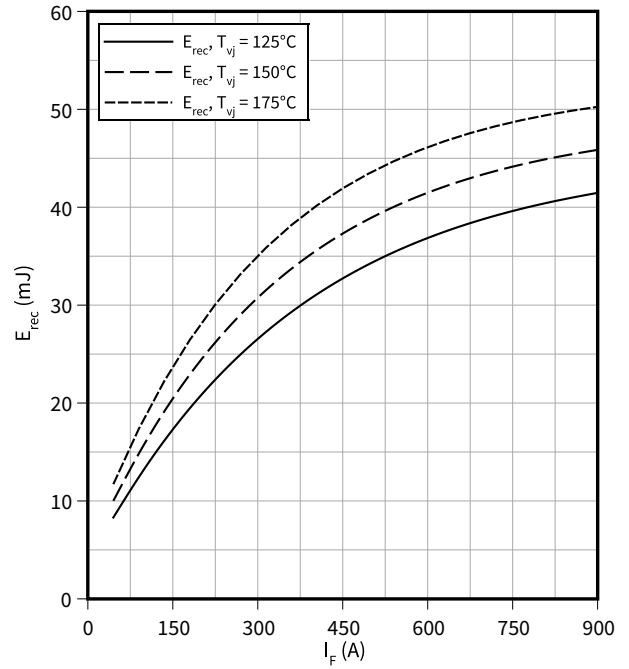
$I_F = f(V_F)$



Switching losses (typical), Diode, D1 / D2

$E_{rec} = f(I_F)$

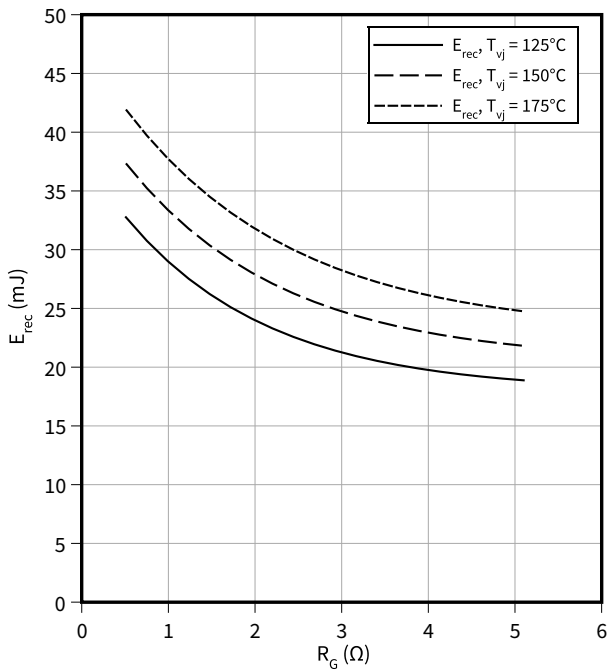
$R_{Gon} = 0.51 \Omega, V_{CE} = 600 \text{ V}$



Switching losses (typical), Diode, D1 / D2

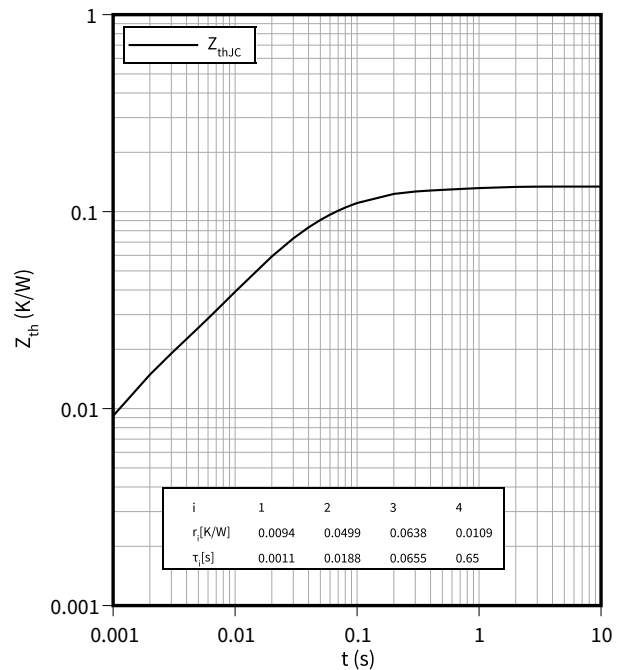
$E_{rec} = f(R_G)$

$V_{CE} = 600 \text{ V}, I_F = 450 \text{ A}$



Transient thermal impedance, Diode, D1 / D2

$Z_{th} = f(t)$



5 Circuit diagram

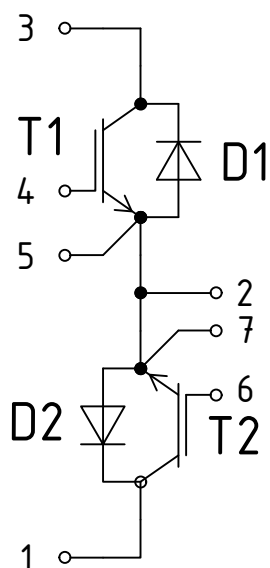


Figure 1

6 Package outlines

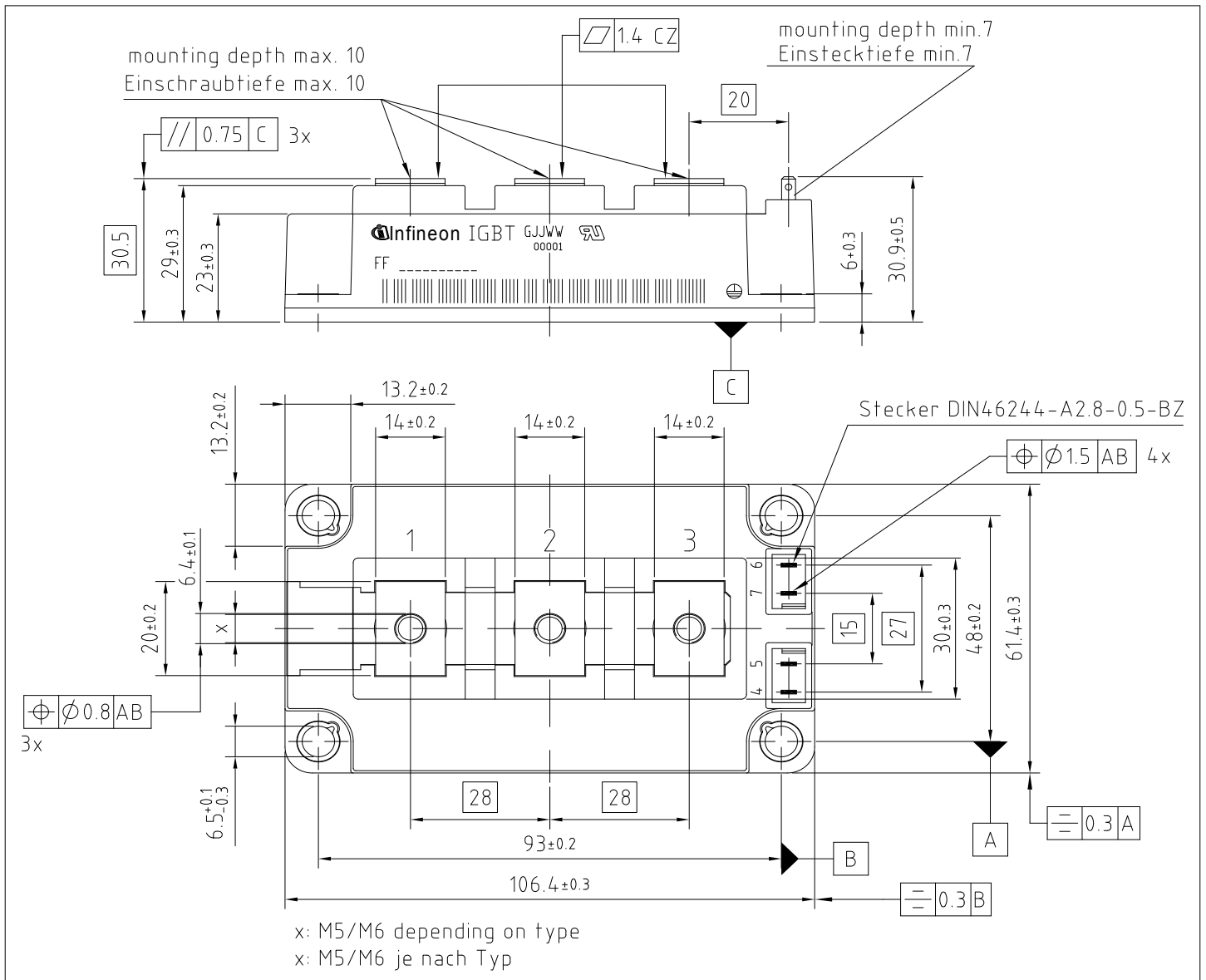


Figure 2

7 Module label code

Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 - 5 6 - 11 12 - 19 20 - 21 22 - 23	<i>Example</i> 71549 142846 55054991 15 30
Example	<div style="display: flex; justify-content: space-around; align-items: center;"> <div style="text-align: center;">  71549142846550549911530 </div> <div style="text-align: center;">  71549142846550549911530 </div> </div>		

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2023-02-24	Preliminary datasheet
1.00	2023-06-19	Final datasheet

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Edition 2023-06-19

Published by

Infineon Technologies AG

81726 Munich, Germany

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Document reference

IFX-ABG627-002

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